



ICSCRM Manuscript Folder Location Guide

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3166	Adedeji	Adetayo	Composite Ohmic Contacts to SiC for High Temperature Applications
3719	Adjaye	John	The Role of Residual Source/Drain Implant Damage Traps on SiC MESFET Drain I-V Characteristics
3666	Agarwal	Anant	Influence of Basal Plane Dislocation Induced Stacking Faults on the Current Gain in SiC BJTs
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3250	As	Donat	Molecular Beam Epitaxy of Cubic Group III-Nitrides on Free-Standing 3C-SiC Substrates
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3219	Awad	Yousef	Physical and Optical Properties of In-Situ Nitrogenated Amorphous Silicon Carbide Films Prepared by a novel Polymer Source Chemical Vapor Deposition (PS-CVD) Technique
3729	Bai	Jie	Strain Relaxation Mechanisms in GaN Films Grown on Vicinal SiC Substrates
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3778	Balachandran	Santhosh	Performance Assessment of 4H-SiC Bipolar Junction Transistors and Insulated Gate Bipolar Transistors
3691	Basceri	Cem	Micropipe-Free Single Crystal Silicon Carbide (SiC) Ingots via Physical Vapor Transport (PVT)
3375	Bassim	Nabil	Transmission Electron Microscopy Investigation of the Role of Surface Steps in the Generation of Misfit Dislocations during MOCVD Growth of GaN on 4H-SiC
3620	Belousov	Mikhail	In-Situ Stress Monitoring by Single Beam Deflectometer
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3392	Bhatnagar	Praneet	Analytical Modelling of I-V Characteristics for 4H-SiC VJFET
3624	Blanc	Caroline	Process Optimisation for $4H-SiC$ MOSFET Applications
3559	Bluet	Jean-Marie	Formation, Morphology and Optical Properties of 4H-SiC Nanoparticles Obtained from Nano-Grinding of Bulk Porous SiC Nanostructures
3835	Blumenau	Alexander	Theory of Dislocations in SiC
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3634	Bogart	Timothy	Microwave Loss Dielectric Characterization of Silicon Carbide Wafers
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3496	Boltovets	Mykola	CM-Wave Modulator with High-Voltage 4H SiC Pin Diodes
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3732	Cao	Xian-An	Structural Properties and Electrical Characteristics of Homoepitaxial GaN PiN Diodes
3387	Capano	Michael	Structural Defects and Critical Electric Field in 3C-SiC
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3406	Chandrashekar	M. V.S.	Demonstration of a 4H SiC Betavoltaic Cell



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3725	Dhanaraj	Govindhan	Growth and Surface Morphologies of 6H SiC Bulk and Epitaxial Crystals
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3792	Dominique	Tournier	4.5 kV- 8A SiC-Schottky Diodes / Si-IGBT Modules
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3410	Drachev	Roman	Fundamental Limitations of SiC PVT Growth Reactors with Cylindrical Heaters
3598	Du	Hui	Relaxation Mechanism of the Defect-Free 3C-SiC Epitaxial Films Grown on Step-Free 4H SiC Mesas
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3681	Gupta	Avinash	Growth and Characterization of Large Diameter 6H and 4H SiC Single Crystals
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3623	Hassan	Jawad	Temperature and Intensity Dependent Carrier Lifetime Measurements on n- and p-Type 4H-SiC Measured by Different Experimental Techniques
3495	Hatakeyama	Tetsuo	Optimization of SiC Super-SBD Based on Scaling Properties of Power Devices
3431	Hatayama	Tomoaki	High Purity SiC Epitaxial Growth by Chemical Vapor Deposition Using CH₃SiH₃ and C₃H₈ Source
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3176	Ivanov	Pavel	The Effect of Temperature on Base Current Gain in Power 4H-SiC BJTs (Physical Analysis)
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3494	Kinoshita	Akimasa	Effect of Surface Orientation and Off-Angle on Surface Roughness and Electrical Properties of p-Type Impurity Implanted 4H-SiC Substrate After High Temperature Annealing
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3398	Krishnaswami	Sumi	A Study on the Reliability and Stability of High Voltage 4H-SiC MOSFET Devices
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3420	Nakao	Hiroshi	Characterization of 4H-SiC MOSFETs Formed on the Different Trench Sidewalls
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